

Amendments to the Specification:

Please replace the paragraphs at page 4, lines 4-19, with the following amended paragraphs:

Figs. 1A-1E are ~~[[a]]~~ cross-sectional ~~[[view]]~~ views illustrating a process sequence for fabricating a TFT in accordance with the present invention;

Figs. 2A-2E ~~[[a]]~~ cross-sectional ~~[[view]]~~ views illustrating another process sequence for fabricating a TFT in accordance with the invention;

Figs. ~~[[3A-3E]]~~ 3A-3D are ~~[[a]]~~ cross-sectional ~~[[view]]~~ views illustrating a further process sequence for fabricating a TFT in accordance with the invention;

Figs. 4A-4D are ~~[[a]]~~ cross-sectional ~~[[view]]~~ views illustrating a process sequence for fabricating a crystalline silicon film in accordance with the invention;

Figs. 5A-5E are ~~[[a]]~~ cross-sectional ~~[[view]]~~ views illustrating another process sequence for fabricating a crystalline silicon film in accordance with the invention; and

Figs. 6A-6F are ~~a-view~~ views illustrating various commercial products using TFTs in accordance with the invention.

Please replace the paragraph beginning at page 7, line 4, with the following amended paragraph:

Phosphorus and nickel are bonded in various forms such as NiP, ~~[[NiP₂]]~~ NiP₂, and ~~[[Ni₂P]]~~ Ni₂P. In addition, these forms are very stable. Compounds of phosphorus and nickel are collectively known as nickel phosphides. Therefore, owing to the heat treatment described above, nickel element has moved into the regions 108 and 110 from the regions ~~[[109]]~~ 100 and ~~[[110]]~~ 109, as shown in Fig. 1D. In particular, the concentration of nickel phosphides in the regions 108 and 110 increases.

Concomitantly, the nickel concentration in the regions 100 and 109 decreases. In this state, nickel element has been gettered into the source and drain regions (Fig. 1D).